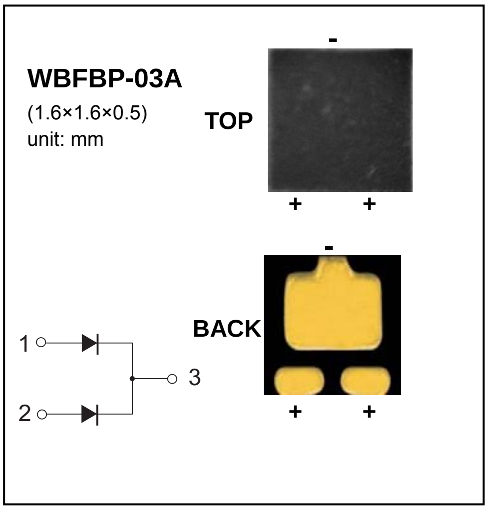
JCST

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03A Plastic-Encapsulate Diodes



DKN222TTD03 SWITCHING DIODE

DESCRIPTION

Epitaxial planar silicon diode

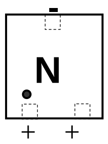
FEATURES:

High speed
Suitable for high packing density layout
High reliability

APPLICATION

Ultra high speed switching
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING: N



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	80	V
DC reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	300	mA
Average forward current	I_O	100	mA
Power dissipation	P_D	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	80		V
Reverse voltage leakage current	I_R	V_R=70V		0.1	μA
Forward voltage	V_F	I_F=100mA		1.2	V
Diode capacitance	C_D	V_R=6V, f=1MHz		3.5	pF
Reverse recovery time	t_{rr}	V_R=6V, I_F=5mA		4	ns

A,Jun,2011